



TISP4070J3BJ THRU TISP4395J3BJ

BIDIRECTIONAL THYRISTOR OVERVOLTAGE PROTECTORS

TISP4xxxJ3BJ Overvoltage Protector Series

Ion-Implanted Breakdown Region
-Precise and Stable Voltage
-Low Voltage Overshoot Under Surge

Designed for Transformer Center Tap (Ground Return) Overvoltage Protection
-Enables GR-1089-CORE Compliance
-High Holding Current Allows Protection of Data Lines with d.c. Power Feed

Can be Used to Protect Rugged Modems Designed for Exposed Applications Exceeding TIA-968-A

Device Name	V_{DRM} V	$V_{(BO)}$ V
TISP4070J3BJ	58	70
TISP4080J3BJ	65	80
TISP4095J3BJ	75	95
TISP4115J3BJ	90	115
TISP4125J3BJ	100	125
TISP4145J3BJ	120	145
TISP4165J3BJ	135	165
TISP4180J3BJ	145	180
TISP4200J3BJ	155	200
TISP4219J3BJ	180	219
TISP4250J3BJ	190	250
TISP4290J3BJ	220	290
TISP4350J3BJ	275	350
TISP4395J3BJ	320	395



..... **UL Recognized Component**

SMB Package (Top View)



MD-SMB-004-a

Device Symbol



SD-TISP4xxx-001-a

Rated for International Surge Wave Shapes

Wave Shape	Standard	I_{PPSM} A
2/10	GR-1089-CORE	1000
8/20	IEC 61000-4-5	800
10/160	TIA-968-A	400
10/700	ITU-T K.20/21/45	350
10/560	TIA-968-A	250
10/1000	GR-1089-CORE	200

Description

The range of TISP4xxxJ3BJ devices are designed to limit overvoltages on telecom lines. The TISP4xxxJ3BJ is primarily designed to address GR-1089-CORE compliance on data transmission lines with d.c. power feeding. When overvoltage protection is applied to transformer coupled lines from the transformer center tap to ground, the total ground return current can be 200 A, 10/1000 and 1000 A, 2/10. The high 150 mA holding current is set above common d.c. feed system levels to allow the TISP4xxxJ3BJ to reset following a disturbance.

These devices allow signal voltages, without clipping, up to the maximum off-state voltage value, V_{DRM} , see Figure 1. Voltages above V_{DRM} are limited and will not exceed the breakdown voltage, $V_{(BO)}$, level. If sufficient current flows due to the overvoltage, the device switches into a low voltage on-state condition, which diverts the current from the overvoltage through the device. When the diverted current falls below the holding current, I_H , level the device switches off and restores normal system operation.

How to Order

Device	Package	Carrier	Order As	Marking Code	Std. Qty.
TISP4xxxJ3BJ	SMB (DO-214AA)	Embossed Tape Reeled	TISP4xxxJ3BJR-S	4xxxJ3	3000

Insert xxx value corresponding to device name.

*RoHS Directive 2002/95/EC Jan. 27, 2003 including annex and RoHS Recast 2011/65/EU June 8, 2011.

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Absolute Maximum Ratings, $T_A = 25^\circ\text{C}$ (Unless Otherwise Noted)

Rating	Symbol	Value	Unit	
Repetitive peak off-state voltage	V_{DRM}	'4070J3BJ	± 58	
		'4080J3BJ	± 65	
		'4095J3BJ	± 75	
		'4115J3BJ	± 90	
		'4125J3BJ	± 100	
		'4145J3BJ	± 120	
		'4165J3BJ	± 135	
		'4180J3BJ	± 145	
		'4200J3BJ	± 155	
		'4219J3BJ	± 180	
		'4250J3BJ	± 190	
		'4290J3BJ	± 220	
		'4350J3BJ	± 275	
		'4395J3BJ	± 320	
Non-repetitive peak impulse current (see Notes 1 and 2)				
2/10 μs (GR-1089-CORE, 2/10 μs voltage wave shape)		± 1000		
8/20 μs (IEC 61000-4-5, combination wave generator, 1.2/50 μs voltage wave shape)		± 800		
10/160 μs (TIA-968-A, 10/160 μs voltage wave shape)		± 400		
4/250 μs (ITU-T K.20/21, 10/700 μs voltage waveshape, simultaneous)		± 370		
5/310 μs (ITU-T K.20/21, 10/700 μs voltage wave shape, single)		± 350		
5/320 μs (TIA-968-A, 9/720 μs voltage waveshape, single)		± 350		
10/560 μs (TIA-968-A, 10/560 μs voltage wave shape)		± 250		
10/1000 μs (GR-1089-CORE, 10/1000 μs voltage wave shape)		± 200		
Non-repetitive peak on-state current (see Notes 1 and 2)				
20 ms, 50 Hz (full sine wave)		I_{TSM}	50	
Initial rate of rise of on-state current. Linear current ramp. Maximum ramp value < 50 A		dI/dt	800 A/ μs	
Junction temperature		T_J	-40 to +150 $^\circ\text{C}$	
Storage temperature range		T_{stg}	-65 to +150 $^\circ\text{C}$	

NOTES: 1. Initially the device must be in thermal equilibrium with $T_J = 25^\circ\text{C}$.

2. These non-repetitive rated currents are peak values of either polarity. The surge may be repeated after the device returns to its initial conditions.

Electrical Characteristics, $T_A = 25^\circ\text{C}$ (Unless Otherwise Noted)

Parameter	Test Conditions	Min	Typ	Max	Unit	
I_{DRM}	$V_D = V_{\text{DRM}}$	$T_A = 25^\circ\text{C}$			μA	
$V_{(\text{BO})}$	Repetitive peak off-state current	$T_A = 85^\circ\text{C}$	± 5			
			± 10			
		'4070J3BJ	± 70			
		'4080J3BJ	± 80			
		'4095J3BJ	± 95			
		'4115J3BJ	± 115			
		'4125J3BJ	± 125			
		'4145J3BJ	± 145			
		'4165J3BJ	± 165			
		'4180J3BJ	± 180			
		'4200J3BJ	± 200			
		'4219J3BJ	± 219			
		'4250J3BJ	± 250			
		'4290J3BJ	± 290			
		'4350J3BJ	± 350			
		'4395J3BJ	± 395			
AC Breakover voltage					V	
$dV/dt = \pm 250 \text{ V/ms}$, $R_{\text{SOURCE}} = 300 \Omega$						

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Electrical Characteristics, $T_A = 25^\circ\text{C}$ (Unless Otherwise Noted)

Parameter	Test Conditions	Min	Typ	Max	Unit	
$V_{(BO)}$	Ramp breakdown voltage dv/dt $\leq \pm 1000 \text{ V}/\mu\text{s}$, Linear voltage ramp, Maximum ramp value = $\pm 500 \text{ V}$ di/dt = $\pm 20 \text{ A}/\mu\text{s}$, Linear current ramp, Maximum ramp value = $\pm 10 \text{ A}$	'4070J3BJ '4080J3BJ '4095J3BJ '4115J3BJ '4125J3BJ '4145J3BJ '4165J3BJ '4180J3BJ '4200J3BJ '4219J3BJ '4250J3BJ '4290J3BJ '4350J3BJ '4395J3BJ			± 77 ± 88 ± 104 ± 125 ± 135 ± 156 ± 177 ± 192 ± 212 ± 231 ± 263 ± 303 ± 364 ± 409	V
$I_{(BO)}$	Breakover current dv/dt = $\pm 250 \text{ V}/\text{ms}$, $R_{\text{SOURCE}} = 300 \Omega$	'4070J3BJ thru '4115J3BJ '4125J3BJ thru '4219J3BJ '4250J3BJ thru '4395J3BJ			± 900 ± 800 ± 600	mA
I_H	Holding current $I_T = \pm 5 \text{ A}$, di/dt = $\pm 30 \text{ mA}/\text{ms}$		± 150		± 600	mA
dv/dt	Critical rate of rise of off-state voltage Linear voltage ramp Maximum ramp value $< 0.85V_{\text{DRM}}$		± 5			KV/ μs
I_D	Off-state current $V_D = \pm 50 \text{ V}$			$T_A = 85^\circ\text{C}$	± 10	μA
C_O	Off-state capacitance $f = 1 \text{ MHz}$, $V_d = 1 \text{ V rms}$, $V_D = 0$	'4070J3BJ thru '4115J3BJ '4125J3BJ thru '4219J3BJ '4250J3BJ thru '4395J3BJ		195 120 105	235 145 125	pF
		'4070J3BJ thru '4115J3BJ '4125J3BJ thru '4219J3BJ '4250J3BJ thru '4395J3BJ		180 110 95	215 132 115	
		'4070J3BJ thru '4115J3BJ '4125J3BJ thru '4219J3BJ '4250J3BJ thru '4395J3BJ		165 100 90	200 120 105	
	$f = 1 \text{ MHz}$, $V_d = 1 \text{ V rms}$, $V_D = -50 \text{ V}$	'4070J3BJ thru '4115J3BJ '4125J3BJ thru '4219J3BJ '4250J3BJ thru '4395J3BJ		85 50 42	100 60 50	
		'4070J3BJ thru '4115J3BJ '4125J3BJ thru '4219J3BJ '4250J3BJ thru '4395J3BJ		40 35	50 40	

NOTE: 3. To avoid possible clipping, the TISP4125J3BJ is tested with $V_D = -98 \text{ V}$.

Thermal Characteristics

Parameter	Test Conditions	Min	Typ	Max	Unit
$R_{\theta JA}$	Junction to ambient thermal resistance EIA/JESD51-3 PCB, $I_T = I_{\text{TSM}(1000)}$ (see Note 4)			90	°C/W

NOTE: 4. EIA/JESD51-2 environment and PCB has standard footprint dimensions connected with 5 A rated printed wiring track widths.

Parameter Measurement Information

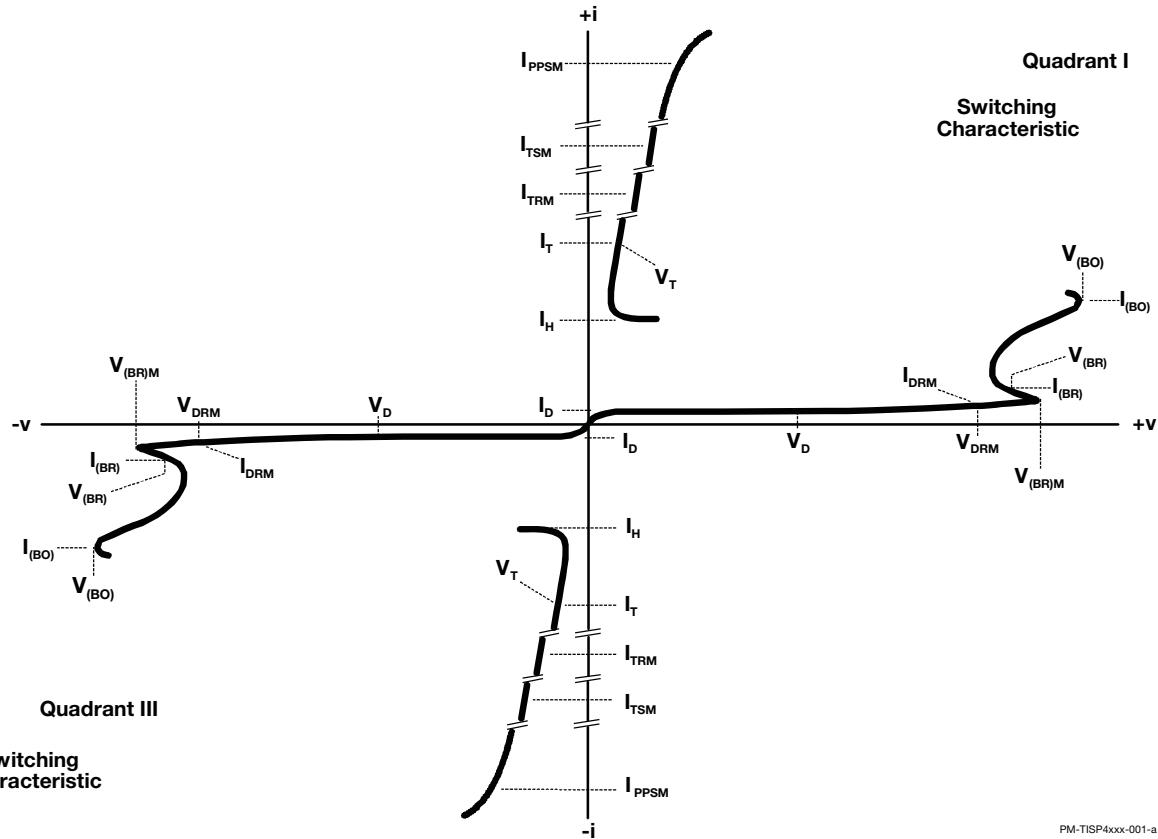


Figure 1. Voltage-Current Characteristic for T and R Terminals
All Measurements are Referenced to the R Terminal

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Typical Characteristics

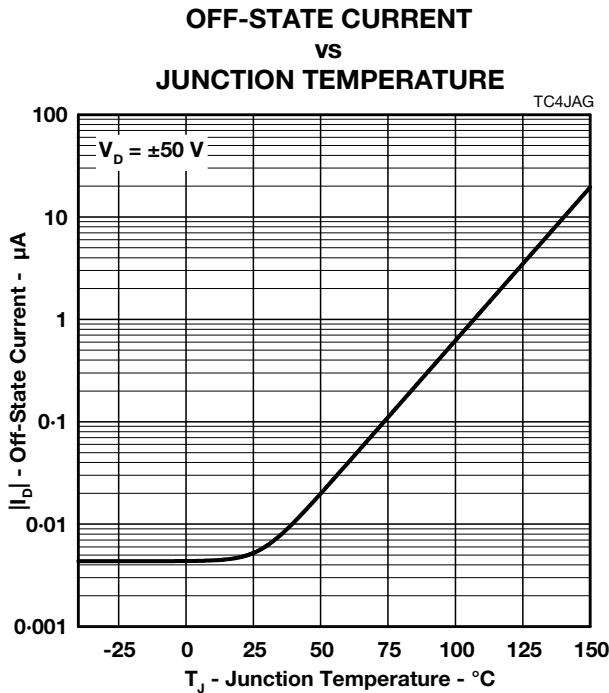


Figure 2.

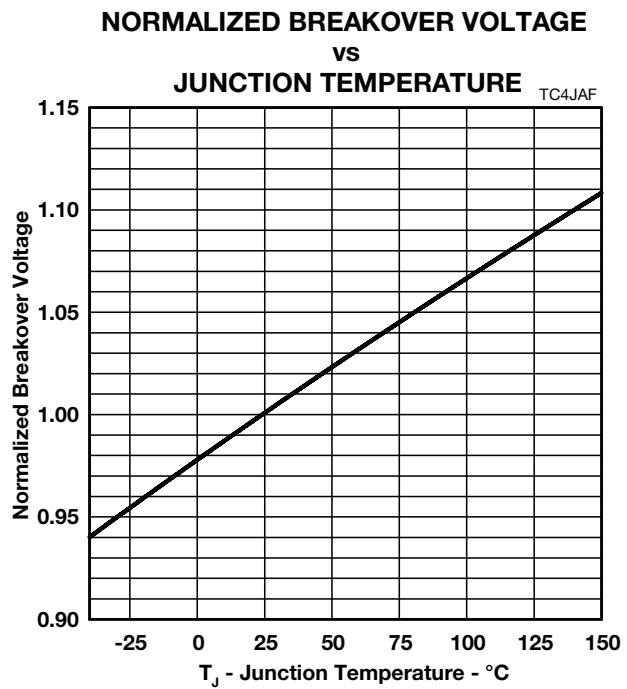


Figure 3.

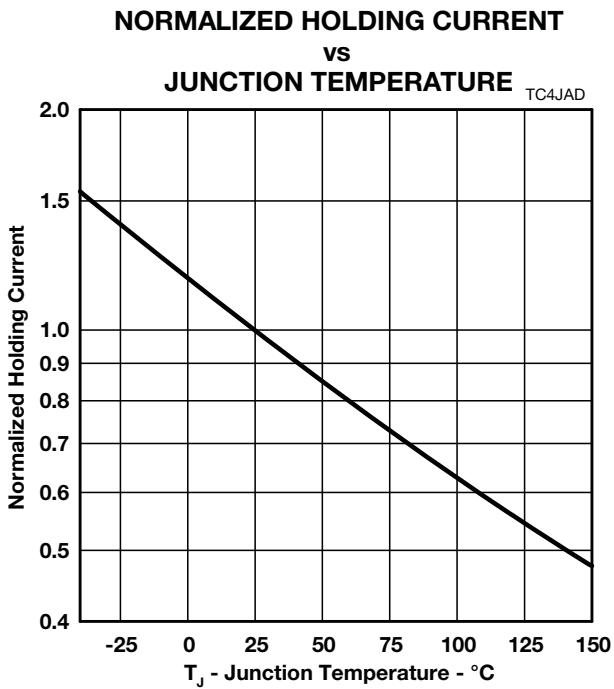


Figure 4.

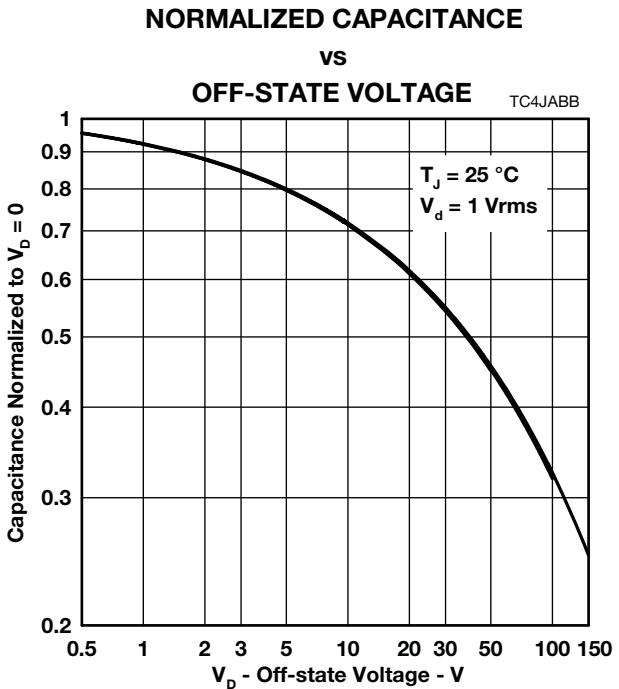


Figure 5.

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Rating and Thermal Characteristics

NON-REPETITIVE PEAK ON-STATE CURRENT vs CURRENT DURATION

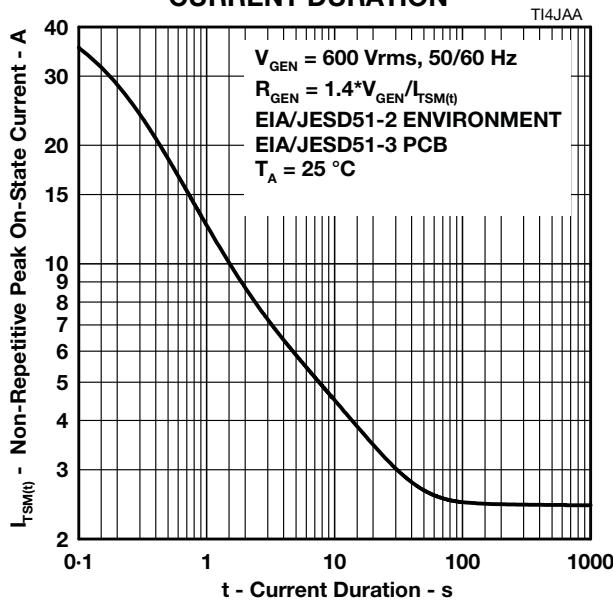


Figure 6.

V_{DRM} DERATING FACTOR

vs MINIMUM AMBIENT TEMPERATURE

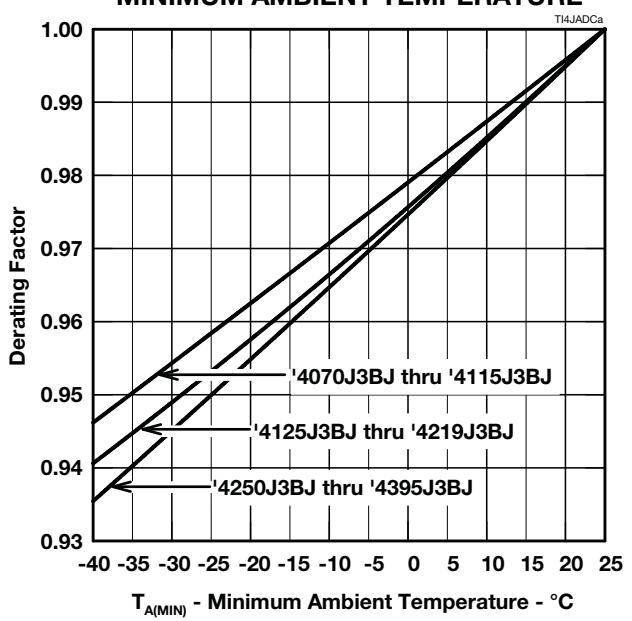


Figure 7.

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Applications Information

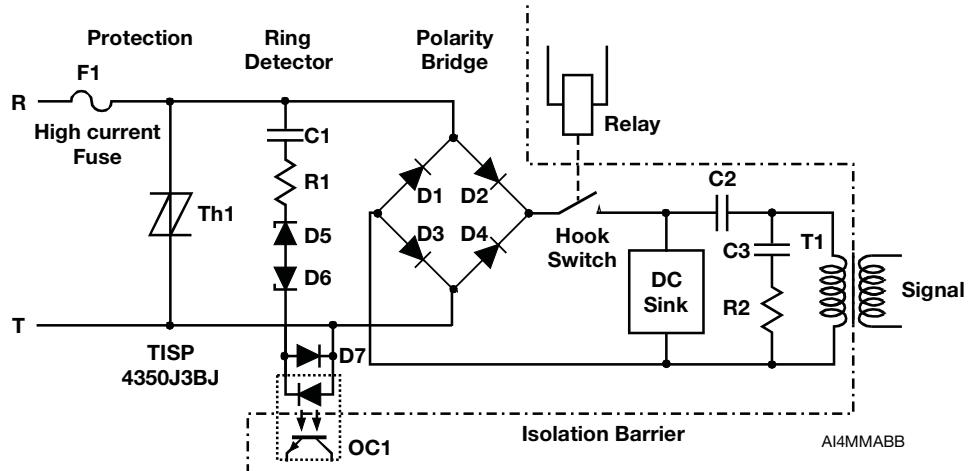


Figure 8. Typical Application Circuit

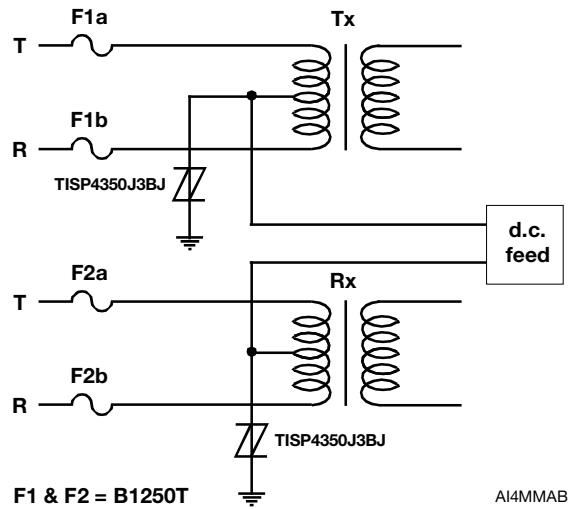


Figure 9. Typical Application Circuit

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